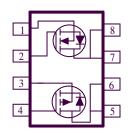
P & N-Channel 30-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY					
$V_{DS}(V)$	$r_{DS(on)}m(\Omega)$	$I_{D}(A)$			
30	$42 @ V_{GS} = 4.5V$	5.8			
30	$28 @ V_{GS} = 10V$	7.1			
-30	$59 @ V_{GS} = -4.5V$	-4.9			
	$39 @ V_{GS} = -10V$	-6.0			

- $\begin{tabular}{ll} \bullet & Low \ r_{DS(on)} \ provides \ higher \ efficiency \ and \\ extends \ battery \ life \end{tabular}$
- Low thermal impedance copper leadframe SOIC-8 saves board space
- Fast switching speed
- High performance trench technology





ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)							
Parameter		Symbol	N-Channel	P-Channel	Units		
Drain-Source Voltage		V_{DS}	30	-30	V		
Gate-Source Voltage			±20	±20	V		
Continuous Drain Current ^a	$T_A=25^{\circ}C$		7.1	-6.0			
Continuous Drain Current	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	1_{D}	5.8	-4.9	A		
Pulsed Drain Current ^b			20	-20			
Continuous Source Current (Diode Conduction) ^a			1.3	-1.3	A		
D C a	$T_A=25^{\circ}C$	D	2.1	2.1	W		
Power Dissipation ^a	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	lr D	1.3	1.3	•••		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150		°C		

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum Units					
N	t <= 10 sec	D	62.5	°C/W			
Maximum Junction-to-Ambient ^a	Steady State	$R_{ heta JA}$	110	°C/W			

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

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Parameter	Symbol	Test Conditions	Ch	Min	Тур	Max	Unit
Static							
Gate-Threshold Voltage	V	$V_{GS} = V_{DS}$, $I_D = 250 \text{ uA}$	N	1			v
Gate-Tilleshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}$, $I_D = -250 \text{ uA}$	P	-1.0			•
Gate-Body Leakage	I_{GSS}	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$	P			±100	nA
	033	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$ $V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$	N P	1		±100	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$	N			1	uА
On-State Drain Current ^A	T	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	N	20			_
On-State Drain Current	$I_{D(on)}$	$V_{DS} = -5 \text{ V}, V_{CS} = -10 \text{ V}$	P	-20			Α
		VGS = 10 V, ID = 7.1 A	N			28 42	
Drain-Source On-Resistance ^A	r _{DS(on)}	$VGS = 4.5 \text{ V}, I_D = 5.8 \text{ A}$ $VGS = -10 \text{ V}, I_D = -6 \text{ A}$				39	mΩ
		VGS = -10 V, ID = -0 A VGS = -4.5 V, ID = -4.9 A	P			59	•
Forward Tranconductance ^A	$V_{DS} = 15 \text{ V},$	$V_{DS} = 15 \text{ V}, I_D = 6.9 \text{ A}$ $V_{DS} = -15 \text{ V}, I_D = -5.2 \text{ A}$	N		25		S
Forward Tranconductance	g_{fs}	$V_{DS} = -15 \text{ V}, I_{D} = -5.2 \text{ A}$	P		10		
Dynamic							
Total Gate Charge	Q_{g}	N. Cl.	N		4.0		
Total Gate Charge	Qg	N-Channel	P N		10		ļ !
Gate-Source Charge	Q_{gs}	$V_{DS} = 15V, V_{GS} = 10V, I_{D} = 6.9A$	P		1.1 2.2		пC
	-	P-Channel V _{DS} =-15V, V _{GS} =-10V, I _D =-5.2A	N		1.4		
Gate-Drain Charge	Q_{gd}	VDS=-13V, VGS=-10V, ID=-3.2A	P		1.7		t
		N	8		+		
Turn-On Delay Time	td(on)	N-Chaneel	P		10		
Rise Time		$V_{DD}=15V$, $V_{GS}=10V$, $I_{D}=1A$,	N		5		
Mise Time	t _r	$R_{\text{GEN}}=6\Omega$,	P		2.8		nS
Turn-Off Delay Time	td(off)	P-Channel	N		23		113
Turn Cri Demy Tine	tu(on)	V_{DD} =-15V, V_{GS} =-10V, I_{D} =-1A		1			
Fall-Time	t_{f}	$R_{GEN}=6\Omega$	N		3		J

Notes

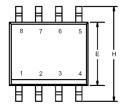
- a. Pulse test: $PW \le 300$ us duty cycle $\le 2\%$.
- b. Guaranteed by design, not subject to production testing.

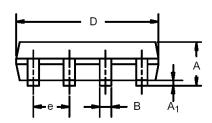
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Package Information

SO-8: 8LEAD





	MILLIM	IETERS	INCHES		
Dim	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
Е	3.80	4.00	0.150	0.157	
е	1.27	BSC	0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	

